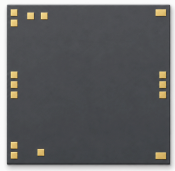
8000–8400 MHz GaN MMIC Power Amplifier Die

LCI-PA-8000-8400-PS45T is a GaN MMIC power amplifier supplied as bare die for 8000–8400 MHz. It supports CW and pulsed operation.

The RF table specifies: Saturated output power: 45 dBm (typical); Power gain: 23 dB (typical); Power-added efficiency: 55 % (typical). RF test conditions: TA = +25 °C; Vd = +28 V; Vg = -3 V. Die dimensions: 2.9 × 2.8 × 0.1 mm.



RF characteristics

TA = +25 °C; Vd = +28 V; Vg = -3 V

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Operating frequency	f	8000	-	8400	MHz
Saturated output power	Psat	-	45	-	dBm
Power gain	Gp	-	23	-	dB
Power-gain flatness	ΔGp	-	-	±0.5	dB
Power-added efficiency	PAE	-	55	-	%
Small-signal gain	S21	-	33	-	dB
Small-signal gain flatness	ΔS21	-	-	±1	dB
Input VSWR	VSWR(in)	-	1.2	1.3	-

DC bias and current

TA = +25 °C

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Drain voltage	Vd	-	28	32	V
Gate voltage	Vg	-3	-3	-2.6	V
Quiescent drain current	Id	-	0.8	-	A
Dynamic drain current	Idd	-	2.3	2.6	A
Dynamic gate current	Igg	-	0.2	1	mA

Absolute limits

Absolute limits; these are not normal operating targets.

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum drain-source voltage	Vd	-	-	32	V
Minimum gate bias	Vg	-5	-	-	V
Maximum input power	Pin	-	-	26	dBm
Maximum channel temperature	Top	-	-	225	°C
Storage temperature	TSTG	-65	-	150	°C

Die dimensions

Parameter	Value	Unit
Die dimensions	2.9 × 2.8 × 0.1	mm
Plan-view outline tolerance	±100 (Plan-view outline only; the source does not specify thickness tolerance.)	µm

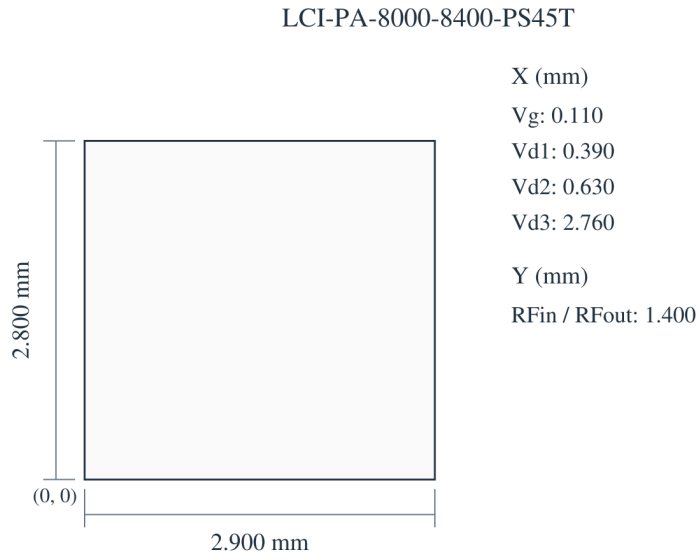
Current publication record · 1.9 · 2026-11-12. Product description or editorial content updated. Replaces revision 1.8.

Die integration and bias sequencing

Apply gate bias before drain bias at power-up. At power-down, remove drain bias before gate bias. Use clean handling, ESD protection and a carrier with thermal expansion compatible with the SiC die.

Mechanical Outline

Outline and dimensioned coordinates in mm. Use this drawing as a dimensional reference. Fabrication and wire bonding require complete drawings.



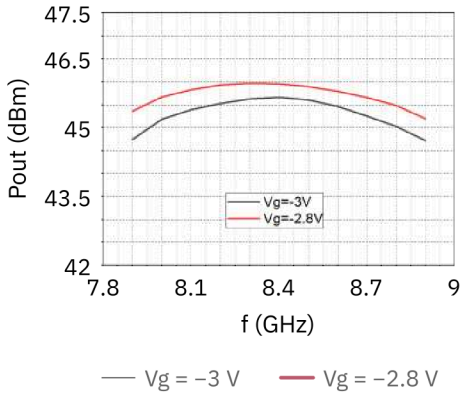
2.900 × 2.800 × 0.100 mm
X, Y: ±0.100 mm
X → · Y ↑ · X, Y: mm

Performance curves

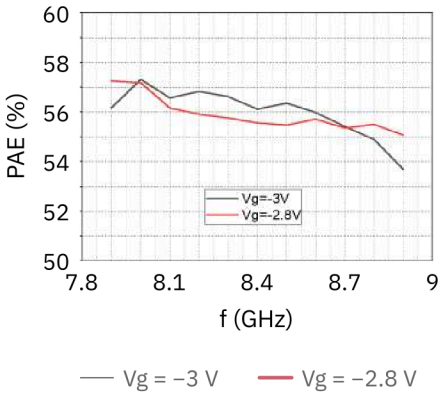
Each performance plot applies to its stated operating conditions.

Pulsed — Saturated output power; Power-added efficiency; Dynamic drain current; Input matching; Gain.

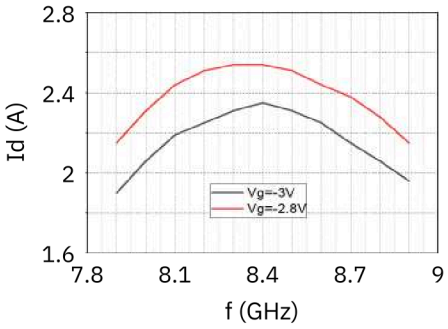
Figure notes: TA = +25°C; Vd=+28V.



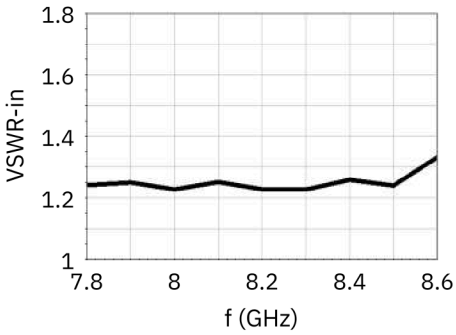
Vg = −3 V Vg = −2.8 V

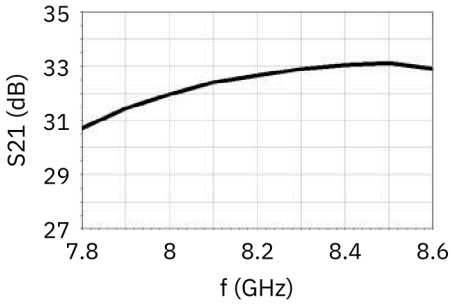


Vg = −3 V Vg = −2.8 V



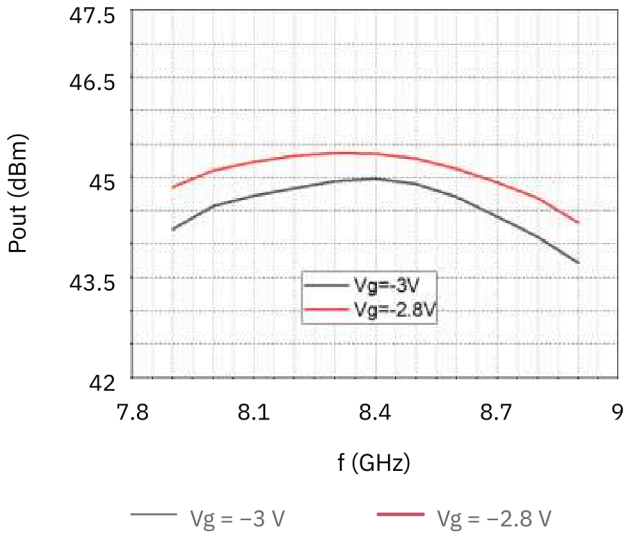
Vg = −3 V Vg = −2.8 V

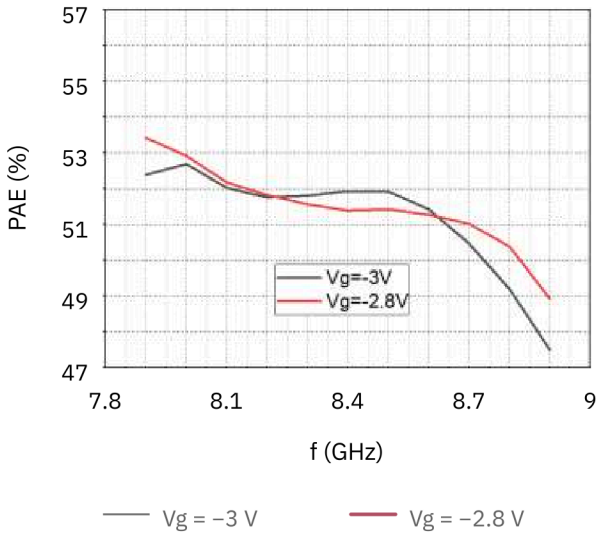


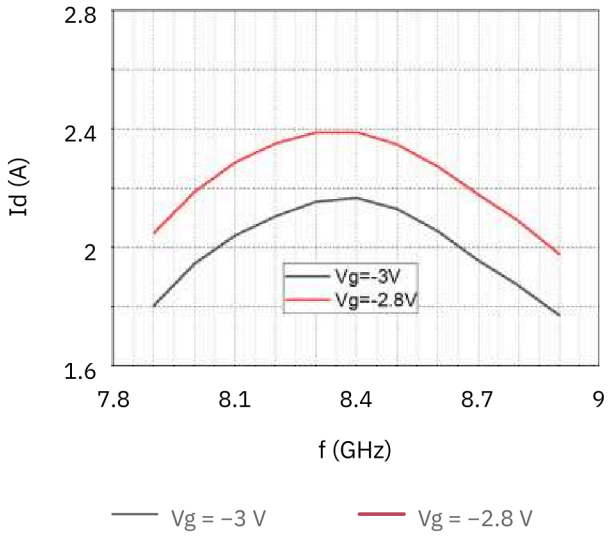


Continuous wave (CW) — Saturated output power; Power-added efficiency; Dynamic drain current.

Figure notes: TA = +25°C; Vd=+28V; Pin=22dBm.

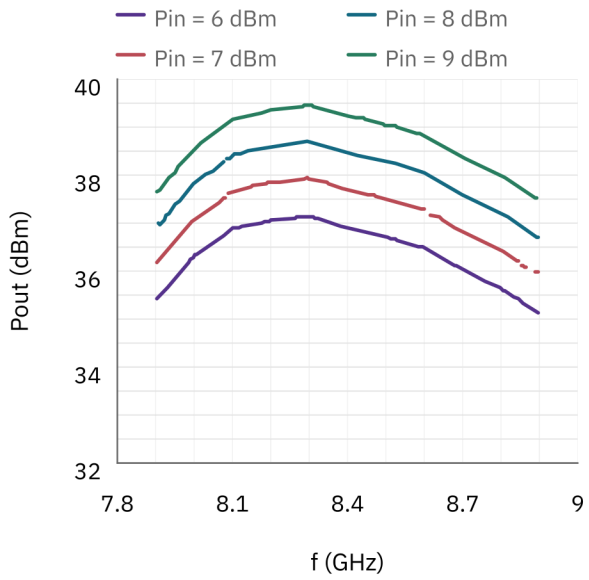


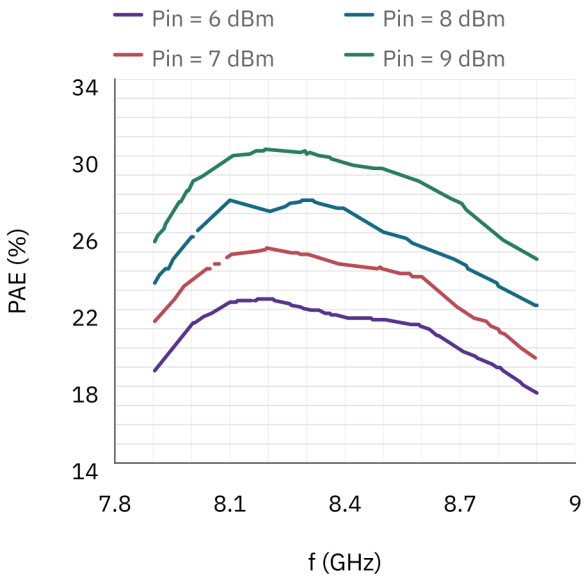


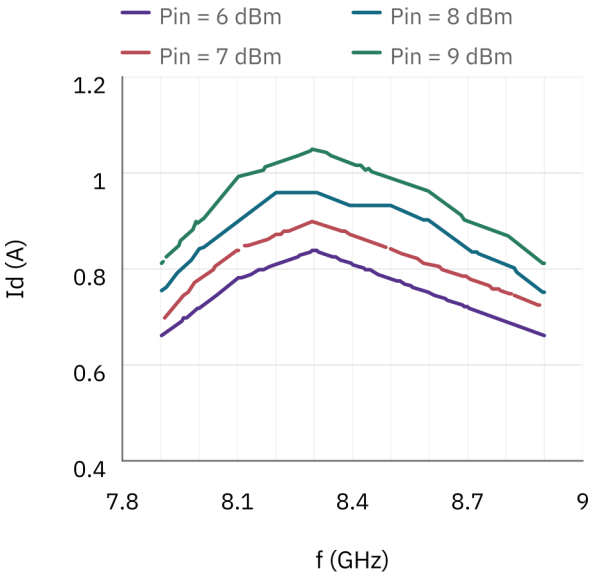


Pulsed — Backed-off output power; Power-added efficiency; Dynamic drain current.

Figure notes: TA = +25°C; Vd=+28V; Vg=-3.0V. Readings are approximate. Pin = 6 / 7 / 8 / 9 dBm. Read each trace with the conditions shown in its plot. Pulse width = 100 µs; duty cycle = 10%.







Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.